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Preliminary

SGA-0163(Z)

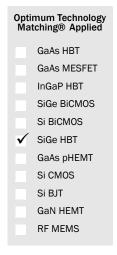
DC to 4500 MHz, SILICON GERMANIUM CASCADABLE GAIN BLOCK

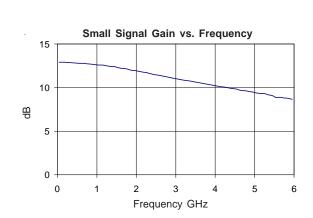
RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)
Package: SOT-363



Product Description

The SGA-0163 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high FT and excellent thermal perfomance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.





Features

- DCto 4500 MHz Operation
- Single Voltage Supply
- Low Current Draw: 8mA at 2.1V typ.
- High Output Intercept: 10dBm Typ. at 1900MHz

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Parameter	Specification			I locit	O andition	
Parameter M	Min.	Тур.	Max.	Unit	Condition	
Output Power at 1dB Compression		-1.8		dBm	850MHz	
		-1.8		dBm	1950MHz	
		-2.4		dBm	2400 MHz	
Third Order Intercept Point		9.4		dBm	850MHz	
		9.8		dBm	1950MHz	
		9.2		dBm	2400MHz	
Small Signal Gain		12.7		dB	850MHz	
		12.0		dB	1950MHz	
		11.6		dB	2400MHz	
3dB Bandwidth		4500		MHz		
Input VSWR		1.6:1			DC to 4500 MHz	
Output VSWR		1.3:1			DC to 4500MHz	
Reverse Isolation		17.6		dB	850MHz	
		18.1		dB	1950MHz	
		18.3		dB	2400MHz	
Noise Figure ^[1]		4.6		dB	1950MHz	
Device Operating Voltage		2.1		V		
Device Operating Current	6	8	10	mA		
Thermal Resistance		255		°C/W	junction - lead	

 $\textbf{Test Conditions: V}_S = \textbf{5V}, \textbf{I}_D = \textbf{8} \textbf{mA Typ., T}_L = 25 \text{ °C. OIP3 Tone Spacing} = \textbf{1} \textbf{MHz}, \textbf{P}_{\textbf{OUT}} \textbf{ per tone} = \textbf{-17} \textbf{ dBm}, \textbf{R}_{\textbf{BIAS}} = \textbf{360} \Omega, \textbf{Z}_S = \textbf{Z}_L = \textbf{50} \Omega, \textbf{Z}_S = \textbf{Z}_L = \textbf{20} \Omega, \textbf{Z}_S = \textbf{20} \Omega,$

Preliminary



Absolute Maximum Ratings

Parameter	Rating	Unit
Device Current (I _D)	16	mA
Device Voltage (V _D)	6	V
RF Input Power	-4	dBm
Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	-40 to +85	°C
Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression: $I_DV_D\!<\!(T_J\!-\!T_L)/R_{TH},j\!-\!I$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Parameter	Specification Specification		Unit	Unit	Condition	
Parameter	Min.	Min. Typ. Max.		Unit	Condition	
Gain		12.9		dB	100MHz	
		12.8		dB	500MHz	
		12.7		dB	850MHz	
		12.0		dB	1950MHz	
		11.6		dB	2400MHz	
		10.6		dB	3500MHz	
Output IP ₃		9.4		dBm	100MHz, Tone spacing=1MHz, P _{OUT} per tone= -17 dBm	
		9.5		dBm	500 MHz, Tone spacing=1MHz, P _{OUT} per tone=-17 dBm	
		9.4		dBm	850 MHz, Tone spacing=1MHz, P _{OUT} per tone=-17 dBm	
		9.8		dBm	1950 MHz, Tone spacing=1MHz, P _{OUT} per tone=-17 dBm	
		9.2		dBm	2400 MHz, Tone spacing=1 MHz, P _{OUT} per tone=-17 dBm	
		9.3		dBm	3500 MHz, Tone spacing=1MHz, P _{OUT} per tone=-17 dBm	
Output P1dB		-1.5		dBm	100MHz	
		-1.5		dBm	500 MHz	
		-1.8		dBm	850MHz	
		-1.8		dBm	1950MHz	
		-2.5		dBm	2400MHz	
		-2.7		dBm	3500MHz	
Input Return Loss		12.5		dB	100MHz	
		12.7		dB	500MHz	
		12.8		dB	850MHz	
		12.4		dB	1950MHz	
		12.1		dB	2400MHz	
		11.8		dB	3500MHz	
Reverse Isolation		17.3		dB	100MHz	
		17.4		dB	500MHz	
		17.6		dB	850MHz	
		18.1		dB	1950MHz	
		18.3		dB	2400MHz	
		18.5		dB	3500MHz	
Noise Figure		4.6		dB	100 MHz, Z _S =50 Ω	
		4.6		dB	500MHz, $Z_S = 50\Omega$	
		4.7		dB	850MHz, Z _S =50Ω	
	1	4.6		dB	1950 MHz, Z_S = 50 Ω	

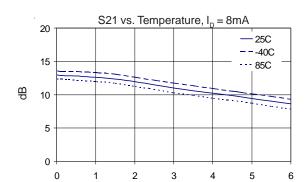
Test Conditions: I_D=8mA, unless otherwise noted



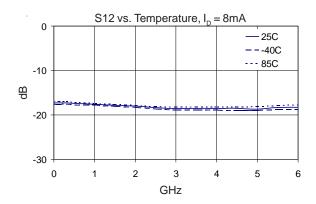
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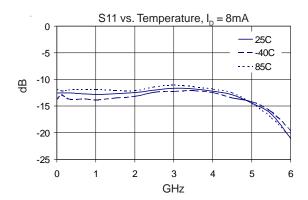
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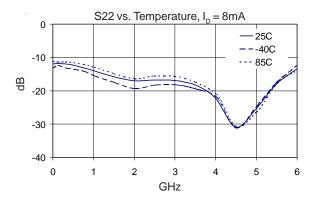
SGA-0163(Z)

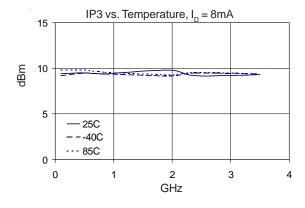


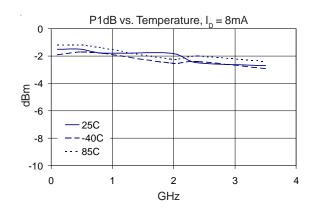
GHz







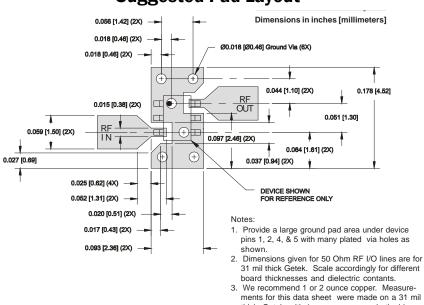






Pin	Function	Description
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
1, 2, 4, 5	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.
6	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.

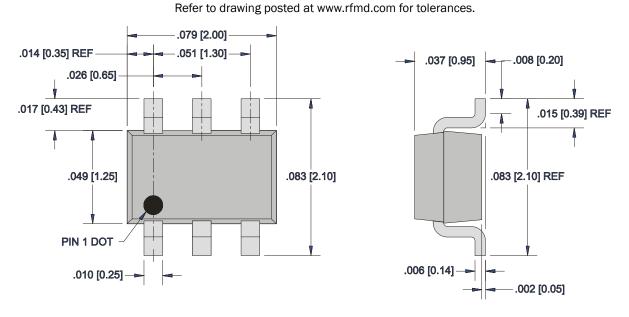
Suggested Pad Layout



- 31 mil thick Getek. Scale accordingly for different
- thick Getek with 1 ounce copper on both sides.

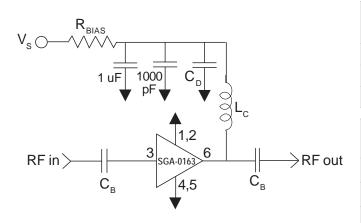
Package Drawing

Dimensions in inches (millimeters)





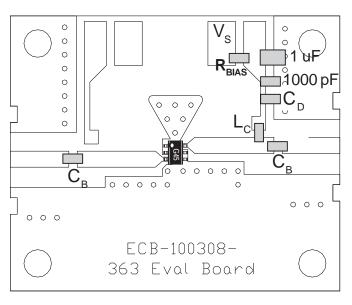
Application Schematic



Reference	Frequency (Mhz)						
Designator	500	850	1950	2400	3500		
C _B	220 pF	100 pF	68 pF	56 pF	39 pF		
C _D	100 pF	68 pF	22 pF	22 pF	15 pF		
L _c	68 nH	33 nH	22 nH	18 nH	15 nH		

Recommended Bias Resistor Values for $I_D=8mA$ $R_{BIAS}=(V_S-V_D)/I_D$					
Supply Voltage(V _s)	5 V	7.5 V	9 V	12 V	
R_{BIAS} 360 Ω 680 Ω 820 Ω 1.2K Ω					
Note: R _{ous} provides DC bias stability over temperature.					

Evaluation Board Layout



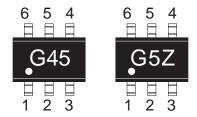
Mounting Instructions

- 1. Use a large ground pad area near device pins 1, 2, 4, and 5 with many plated through-holes as shown.
- We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

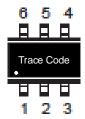
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Part Identification Marking



Alternate Marking with Trace Code Only



Ordering Information

Part Number	Reel Size	Devices/Reel	
SGA-0163	7"	3000	
SGA-0163Z	7"	3000	